UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/564,085	08/16/2006	Tohru Saitoh	061352-0119	7298
	7590 07/21/200 WILL & EMERY LL	EXAMINER		
600 13TH STREET, NW			LI, MEIYA	
WASHINGTON, DC 20005-3096			ART UNIT	PAPER NUMBER
			2811	
			MAIL DATE	DELIVERY MODE
			07/21/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

	Application No.	Applicant(s)		
	10/564,085	SAITOH ET AL.		
Office Action Summary	Examiner	Art Unit		
	MEIYA LI	2811		
The MAILING DATE of this communication ap Period for Reply	pears on the cover sheet with the c	correspondence address		
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D. - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period. - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailir earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATION 136(a). In no event, however, may a reply be tir will apply and will expire SIX (6) MONTHS from the, cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).		
Status				
1) ☐ Responsive to communication(s) filed on 17 A 2a) ☐ This action is FINAL . 2b) ☐ Thi 3) ☐ Since this application is in condition for allowated closed in accordance with the practice under	s action is non-final. ance except for formal matters, pro			
Disposition of Claims				
4) Claim(s) 1-8 is/are pending in the application. 4a) Of the above claim(s) 5 and 6 is/are withdensity is/are allowed. 5) Claim(s) is/are allowed. 6) Claim(s) 1-4,7 and 8 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or are subjected to by the Examination of the drawing(s) filed on 11 January 2006 is/are	rawn from consideration. or election requirement. er.	I to by the Examiner.		
Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E	e drawing(s) be held in abeyance. Section is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).		
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.				
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date 1/11/06,8/16/06.	4) Interview Summary Paper No(s)/Mail D: 5) Notice of Informal F 6) Other:	ate		

Application/Control Number: 10/564,085 Page 2

Art Unit: 2811

DETAILED ACTION

Election/Restrictions

- 1. Applicant's election of species I, claims 1-4, 7 and 8, in the reply filed on April 17, 2009 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).
- 2. Claims 5 and 6 have been withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected invention, there being no allowable generic or linking claim. Election was made **without** traverse in the reply filed on April 17, 2009.

Priority

3. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

4. The information disclosure statement (IDS) submitted on January 11 2006 and August 16, 2006 is in compliance with the provisions of 37 CFR 1.97. Accordingly, the information disclosure statement is being considered by the examiner.

Drawings

5. Figures 23-26 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). Corrected drawings in

Application/Control Number: 10/564,085 Page 3

Art Unit: 2811

compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. The replacement sheet(s) should be labeled "Replacement Sheet" in the page header (as per 37 CFR 1.84(c)) so as not to obstruct any portion of the drawing figures. If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 112

- 6. The following is a quotation of the second paragraph of 35 U.S.C. 112:

 The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.
- 7. Claims 1-4, 7 and 8 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- 8. The claimed limitation of "silicon", as recited in claims 1, 2, 3 and 7, is unclear as to which silicon applicant refers.
- 9. The claimed limitation of "the silicon", as recited in claims 1 and 2, is unclear as to which silicon applicant refers.
- 10. The claimed limitation of "germanium", as recited in claims 3 and 7, is unclear as to which germanium applicant refers.

Claim Rejections - 35 USC § 103

11. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Application/Control Number: 10/564,085

Art Unit: 2811

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Page 4

12. Claims 1-4, 7 and 8, as best understood, are rejected under 35 U.S.C. 103(a) as being unpatentable over applicant admitted prior art (AAPA).

As for claim 1, AAPA shows in Fig. 24 and related text a bipolar transistor comprising:

a substrate (not shown);

a intrinsic base region 106 having a silicon buffer layer 109 comprised of silicon which is formed on said substrate, and a composition-ratio graded base layer 111 which is formed on the silicon buffer layer and comprises silicon and at least germanium and where a composition ratio of the germanium to the silicon varies in a thickness direction of the composition-ratio graded base layer; and

an extrinsic base region 107 having an extrinsic base formation layer 116 comprised of silicon which is formed on said substrate and adjacent to the silicon buffer layer;

wherein a surface of the extrinsic base formation layer is silicided 108.

AAPA does not disclose that each of the extrinsic base formation layer and the silicon buffer layer has a thickness of not less than 40nm.

It would have been obvious to one having ordinary skill in the art at the time of the invention was made to include each of the extrinsic base formation layer and the silicon buffer layer has a thickness of not less than 40nm, in order to optimize the performance of the device. Furthermore, it has been held that discovering an optimum

value of a result effective variable involves only routine skill in the art. *In re Boesch*, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

Furthermore, it has been held in that the applicant must show that a particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range. *In re Woodruff*, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990). Note that the law is replete with cases in which when the mere difference between the claimed invention and the prior art is some dimensional limitation or other variable within the claims, patentability cannot be found. The instant disclosure does not set forth evidence ascribing unexpected results due to the claimed dimensions. See *Gardner v. TEC Systems, Inc.*, 725 F.2d 1338 (Fed. Cir. 1984), which held that the dimensional limitations failed to point out a feature which performed and operated any differently from the prior art.

As for claim 2, AAPA shows in Fig. 24 and related text a bipolar transistor comprising:

a substrate (not shown);

a intrinsic base region 106 having a silicon buffer layer 109 comprised of silicon which is formed on said substrate, and a composition-ratio graded base layer 111 which is formed on the silicon buffer layer and comprises silicon and at least germanium and where a composition ratio of the germanium to the silicon varies in a thickness direction of the composition-ratio graded base layer; and

an extrinsic base region 107 having an extrinsic base formation layer 116 comprised of silicon which is formed on said substrate and adjacent to the silicon buffer layer;

wherein a surface of the extrinsic base formation layer is silicided 108.

AAPA does not disclose that a thickness of the extrinsic base formation layer is substantially equal to a thickness of the silicon buffer layer.

It would have been obvious to one having ordinary skill in the art at the time of the invention was made to have a thickness of the extrinsic base formation layer is substantially equal to a thickness of the silicon buffer layer, in order to optimize the performance of the device. Furthermore, it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. *In re Boesch*, 617 F.2d 272, 205 USPQ 215 (CCPA 1980).

Furthermore, it has been held in that the applicant must show that a particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range. *In re Woodruff*, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990). Note that the law is replete with cases in which when the mere difference between the claimed invention and the prior art is some dimensional limitation or other variable within the claims, patentability cannot be found. The instant disclosure does not set forth evidence ascribing unexpected results due to the claimed dimensions. See *Gardner v. TEC Systems, Inc.*, 725 F.2d 1338 (Fed. Cir. 1984), which held that the dimensional limitations failed to point out a feature which performed and operated any differently from the prior art.

As for claims 3 and 7, AAPA shows the composition-ratio graded base layer is a silicon germanium graded base layer which comprises silicon and germanium.

As for claims 4 and 8, AAPA shows the silicon buffer layer is comprised of monocrystal and the extrinsic base formation layer is comprised of polycrystal.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to MEIYA LI whose telephone number is (571)270-1572. The examiner can normally be reached on Monday-Friday 7:30AM-5:00PM Eastern Standard Time.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lynne Gurley can be reached on (571) 272-1670. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Application/Control Number: 10/564,085 Page 8

Art Unit: 2811

/Lynne A. Gurley/ Supervisory Patent Examiner, Art Unit 2811

/M. L./ Examiner, Art Unit 2811 7/10/2009